

3A NPN Epitaxial Planar Power Transistor

TIP31CJ3

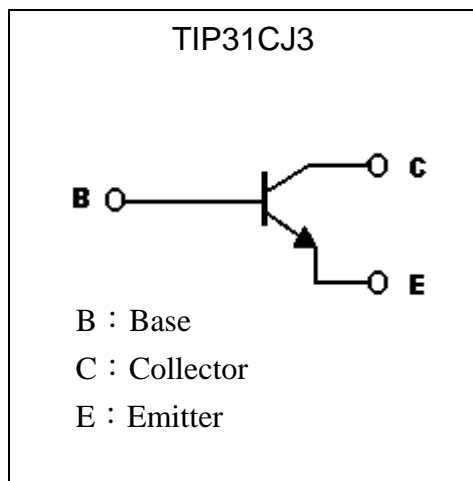
Description

TIP31CJ3 is designed for use in general purpose amplifier and switching applications.

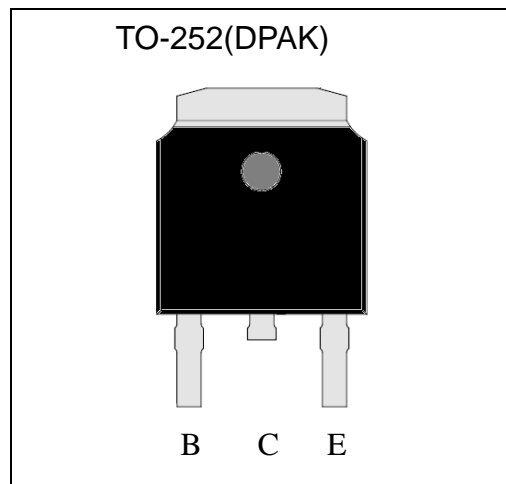
Features

- Low collector-emitter saturation voltage, $V_{CE(sat)} = 0.5V(max) @ I_C = 3A$
- High collector-emitter sustaining voltage, $BV_{CEO(SUS)} = 100V(min)$
- High current gain-bandwidth product , $f_T = 3MHz(min) @ I_C = 500mA$
- Pb-free lead plating and halogen-free package

Symbol

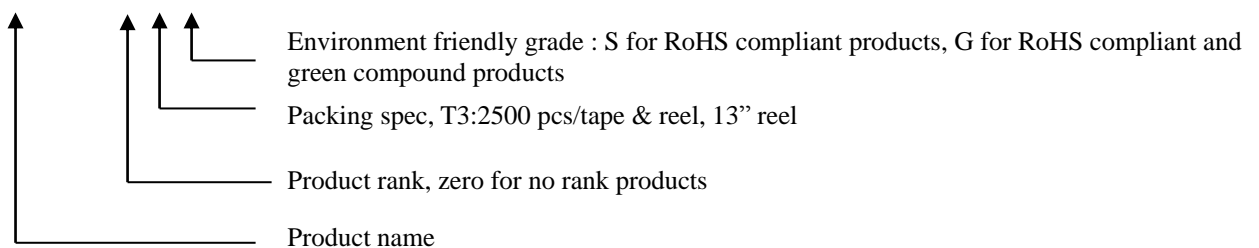


Outline



Ordering Information

Device	Package	Shipping
TIP31CJ3-0-T3-G	TO-252 (Pb-free lead plating and halogen-free package)	2500 pcs / Tape & Reel



Absolute Maximum Ratings (Ta=25°C)

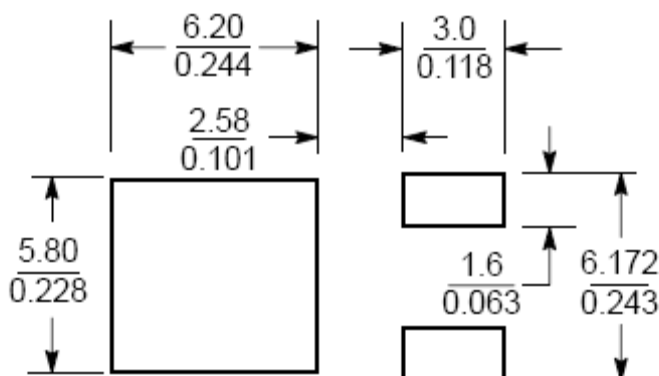
Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CB0}	200	V
Collector-Emitter Voltage	V _{CEO}	100	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current (DC)	I _C	3	A
Collector Current (Pulse)	I _{CP}	5 (Note 1)	
Base Current	I _B	1	A
Power Dissipation @ T _A =25°C	P _D	1.56	W
Power Dissipation @ T _C =25°C	P _D	15	
Thermal Resistance, Junction to Ambient	R _{θJA}	80	°C/W
Thermal Resistance, Junction to Case	R _{θJC}	8.3	°C/W
Operating Junction and Storage Temperature Range	T _j ; T _{stg}	-65~+150	°C

 Note : 1. Single Pulse , P_w ≤ 300μs, Duty ≤ 2%.

Characteristics (Ta=25°C)

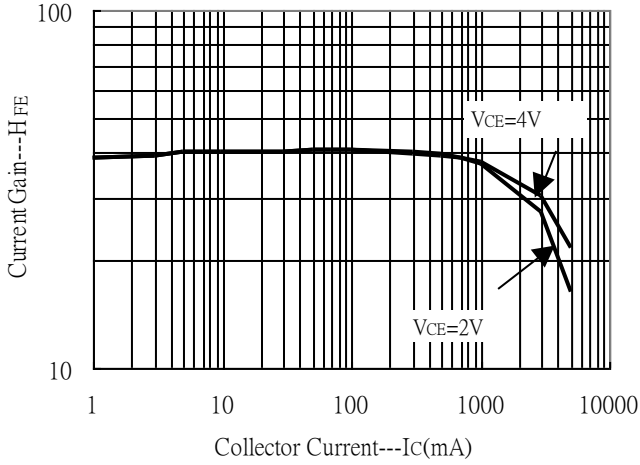
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
*BV _{CEO(SUS)}	100	-	-	V	I _C =30mA, I _B =0
I _{CBO}	-	-	100	nA	V _{CB} =200V, I _C =0
I _{CEO}	-	-	1	μA	V _{CE} =100V, I _B =0
I _{CES}	-	-	1	μA	V _{CE} =100V, V _{BE} =0
I _{EBO}	-	-	100	nA	V _{EB} =5V, I _C =0
*V _{CE(sat)}	-	-	0.5	V	I _C =3A, I _B =375mA
*V _{BE(on)}	-	-	1.2	V	V _{CE} =4V, I _C =3A
*h _{FE}	25	-	-	-	V _{CE} =4V, I _C =1A
*h _{FE}	10	-	50	-	V _{CE} =4V, I _C =3A
f _T	3	-	-	MHz	V _{CE} =10V, I _C =500mA, f=1MHz

*Pulse Test : Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

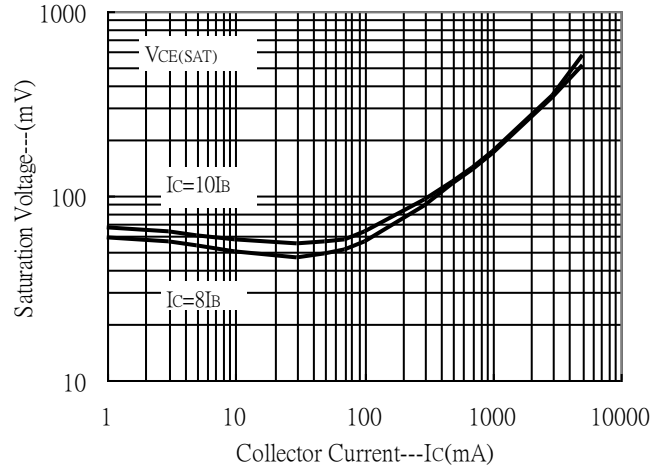
Recommended soldering footprint

 Unit ($\frac{\text{mm}}{\text{inch}}$)

Typical Characteristics

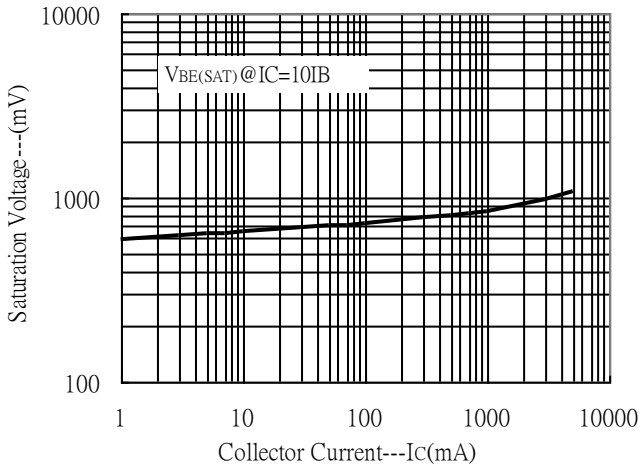
Current Gain vs Collector Current



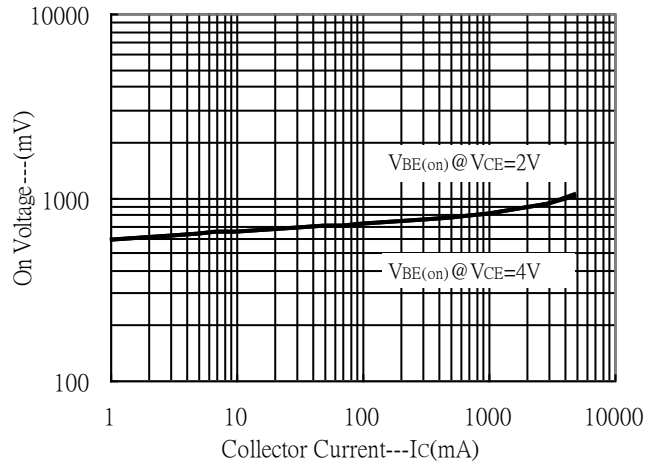
Saturation Voltage vs Collector Current



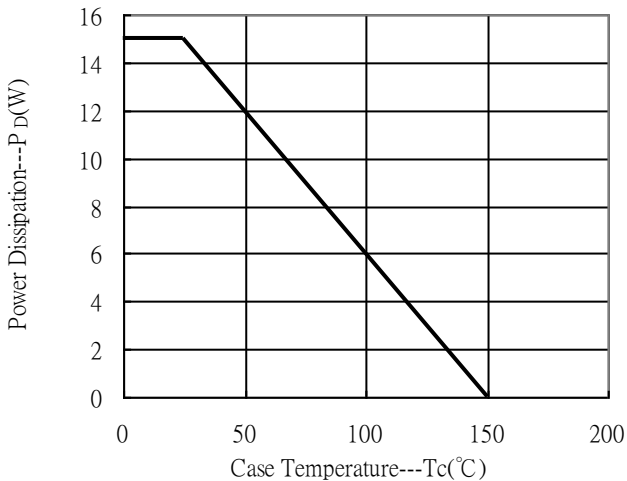
Saturation Voltage vs Collector Current



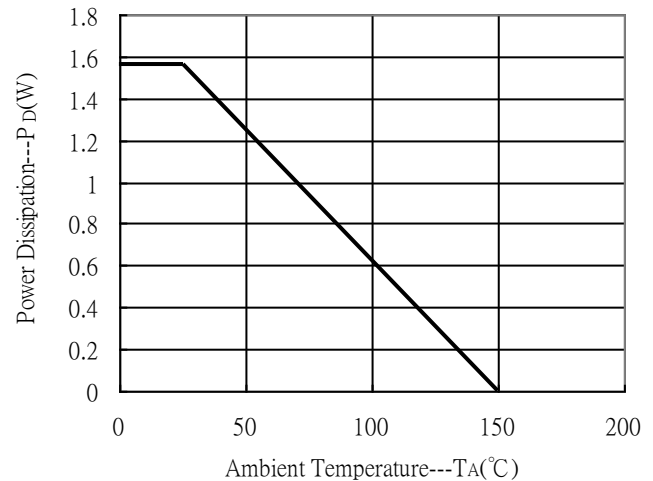
On Voltage vs Collector Current



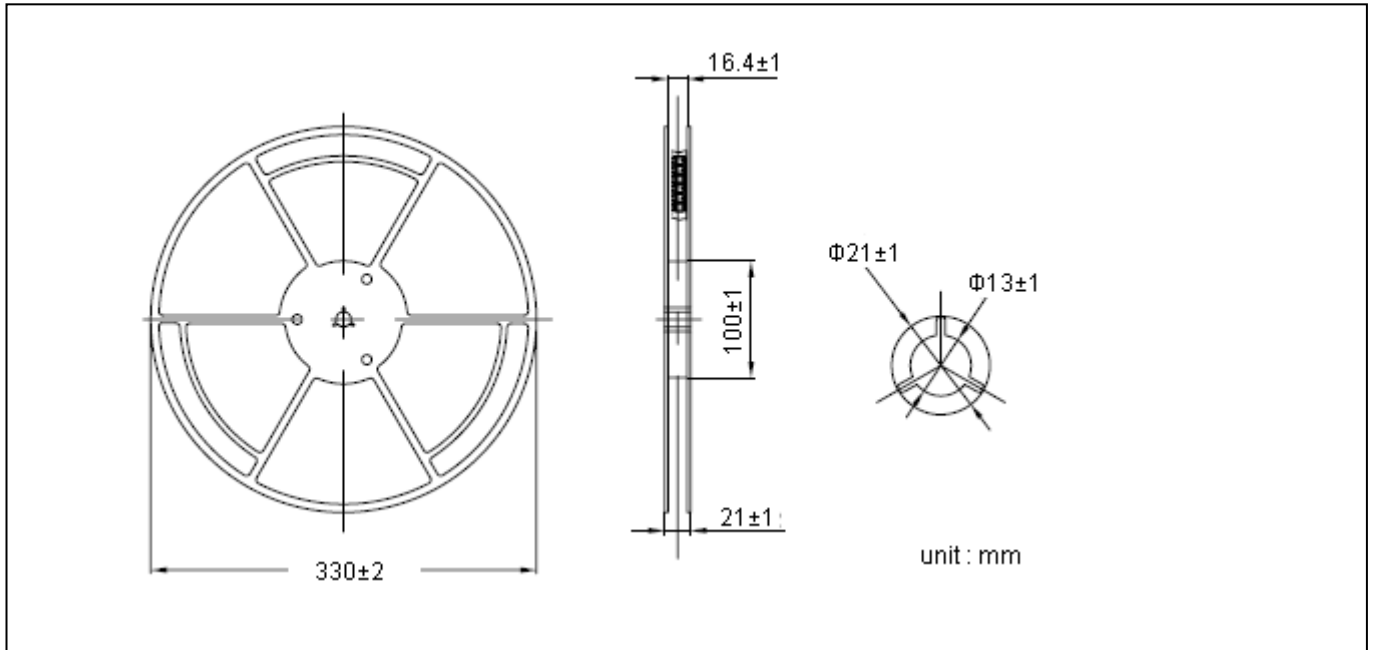
Power Derating Curve



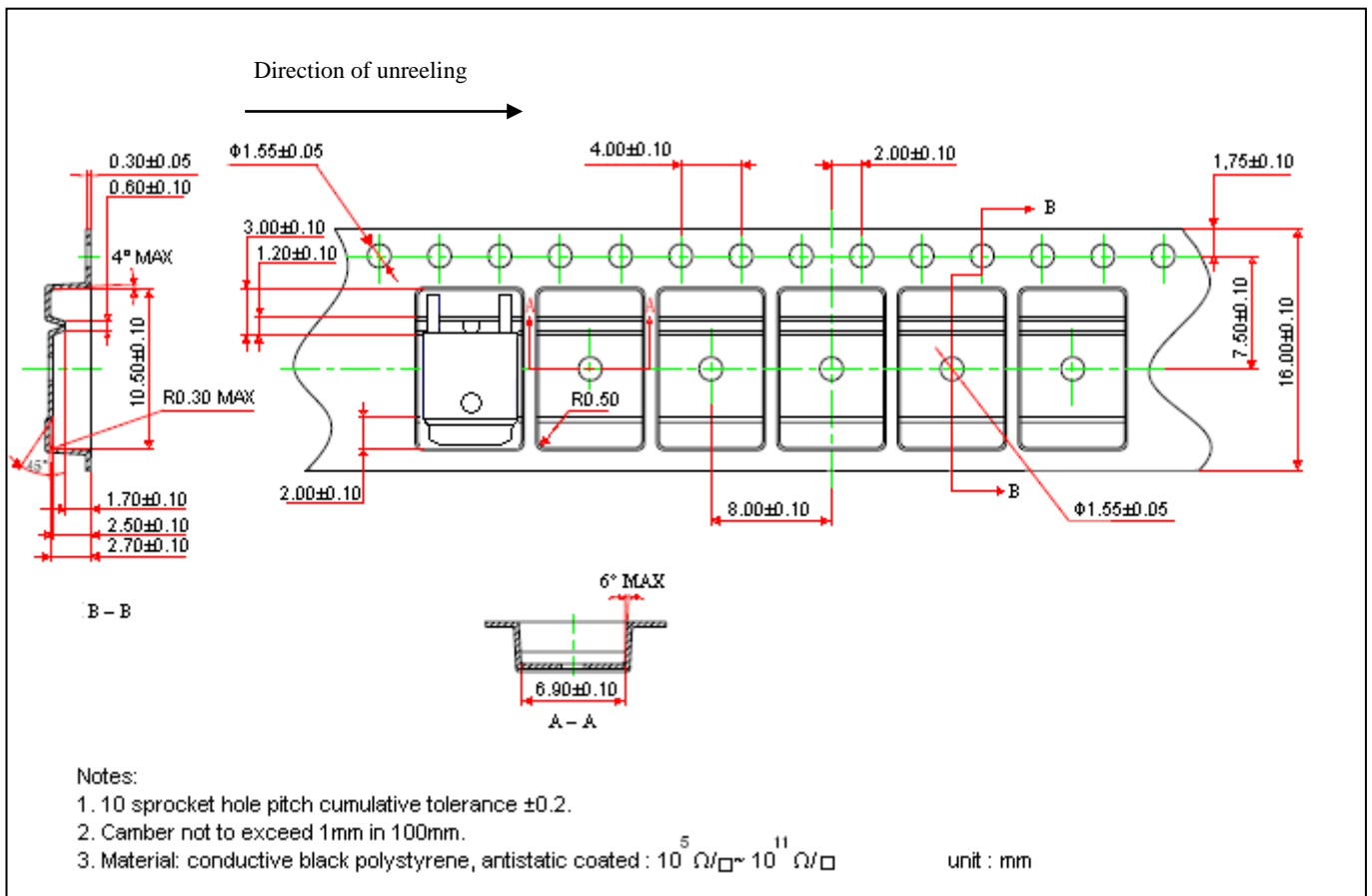
Power Derating Curve



Reel Dimension

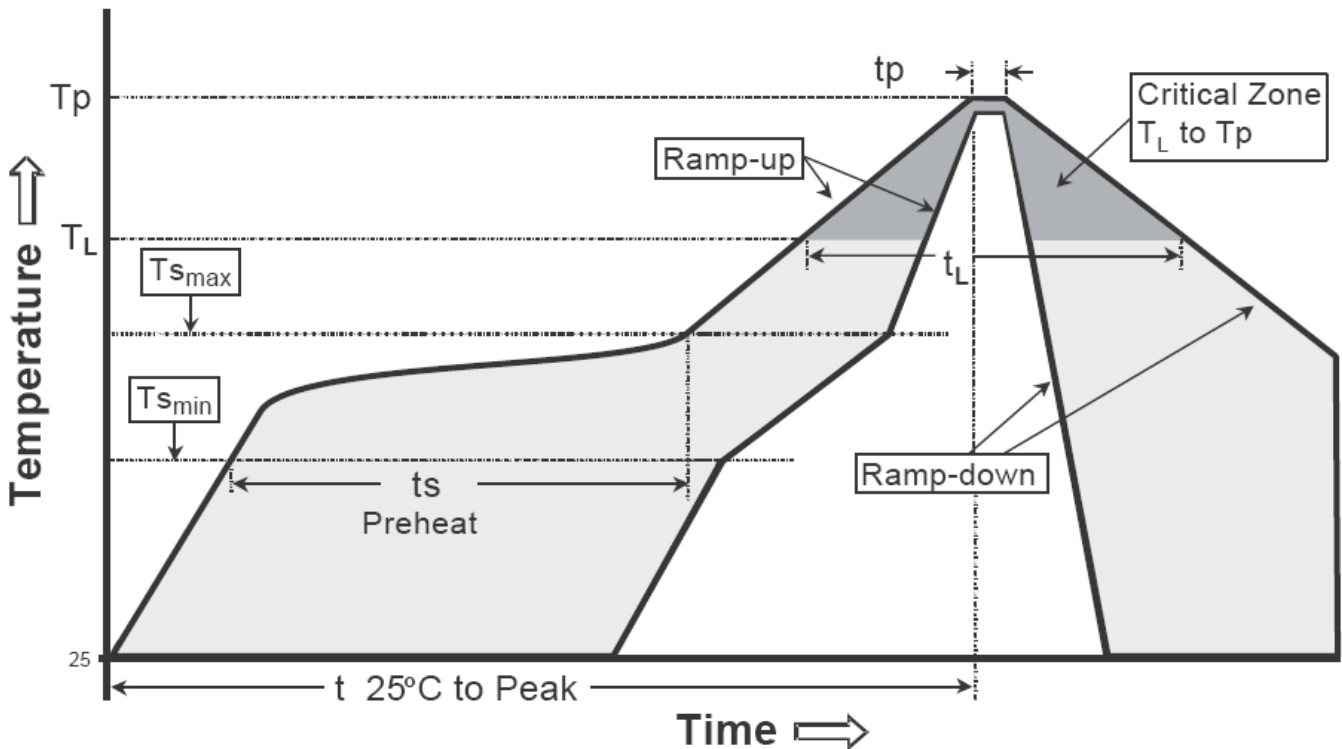


Carrier Tape Dimension



Recommended wave soldering condition

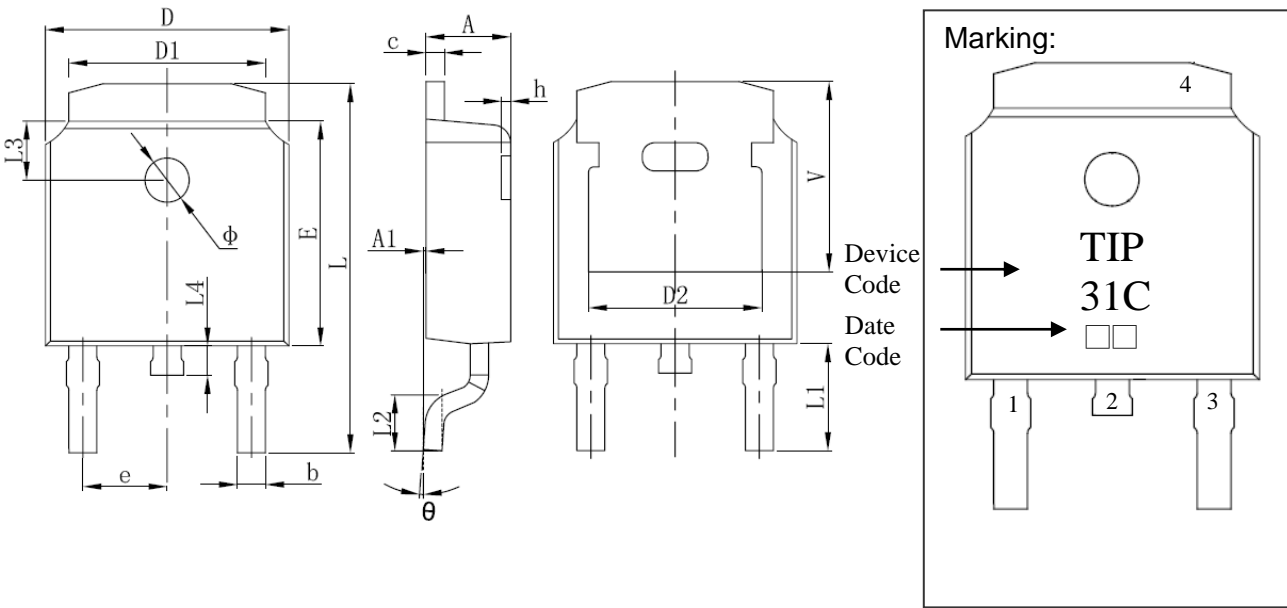
Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(Ts min)	100°C	150°C
-Temperature Max(Ts max)	150°C	200°C
-Time(ts min to ts max)	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (TL)	183°C	217°C
- Time (tL)	60-150 seconds	60-150 seconds
Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

TO-252 Dimension



3-Lead TO-252 Plastic Surface Mount Package
 CYStek Package Code: J3

Date Code :
 First code : Year code, Last digit of Christian Year
 Second Code : Month code, 1~9, A, B, C

Style: Pin 1.Base 2.Collector 3.Emitter
 4.Collector

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	L	0.382	0.406	9.712	10.312
A1	0.000	0.005	0.000	0.127	L1	0.114	REF	2.900	REF
b	0.025	0.030	0.635	0.770	L2	0.055	0.067	1.400	1.700
c	0.018	0.023	0.460	0.580	L3	0.063	REF	1.600	REF
D	0.256	0.264	6.500	6.700	L4	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	Φ	0.043	0.051	1.100	1.300
D2	0.190	REF	4.830	REF	θ	0°	8°	0°	8°
E	0.236	0.244	6.000	6.200	h	0.000	0.012	0.000	0.300
e	0.086	0.094	2.186	2.386	v	0.207	REF	5.250	REF

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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